



# 《风光欣》技术资料

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## 8550S

### PNP EPITAXIAL SILICON TRANSISTOR

#### GENERAL PURPOSE TRANSISTOR

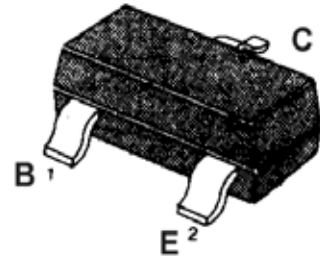
Collector-Emitter Voltage :  $V_{CE0} = -25V$

Collector Dissipation:  $P_c(\max) = 225mW$

#### ABSOLUTE MAXIMUM RATINGS( $T_A = 25$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-40	V
Collector-Emitter Voltage	$V_{CE0}$	-25	V
Emitter -Base Voltage	$V_{EB0}$	-6	V
Collector Current	$I_c$	-500	mA
Collector Dissipation	$P_c$	225	mW
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55 ~150	

SOT-23



#### ELECTRICAL CHARACTERISTICS ( $T_A = 25$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CB0}$	$I_c = -10 \mu A, I_E = 0$	-40			V
*Collector-Emitter Breakdown Voltage	$BV_{CE0}$	$I_c = -1mA, I_B = 0$	-25			V
Emitter-Base Breakdown Voltage	$BV_{EB0}$	$I_E = -10 \mu A, I_c = 0$	-6			V
Collector Cut-off Current	$I_{CB0}$	$V_{CB} = -40V, I_E = 0$			-100	nA
Base Cut-off Current	$I_{EB0}$	$V_{EB} = -5V, I_c = 0$			-100	nA
*DC Current Gain	$H_{FE}$	$V_{CE} = -1V, I_c = -10mA$	85	160	300	
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -50mA, I_B = -5mA$		-0.28	-0.6	V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = -50mA, I_B = -5mA$		-0.98	-1.2	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = -20V, I_c = -10mA, f = 100MHz$	100	200		MHz